

General Purpose Transistor NPN Silicon MMBT4124LT1G

Features

 These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

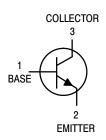
Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	25	Vdc
Collector - Base Voltage	V _{CBO}	30	Vdc
Emitter - Base Voltage	V _{EBO}	5.0	Vdc
Collector Current – Continuous	Ic	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T _A = 25°C Derate above 25°C	P _D	225 1.8	W mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) @T _A = 25°C Derate above 25°C	P _D	300 2.4	W mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.





MARKING DIAGRAM



ZC = Device CodeM = Date Code*= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT4124LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u>.</u>			
Collector – Emitter Breakdown Voltage (Note 3) (I _C = 1.0 mAdc, I _E = 0)	V _{(BR)CEO}	25	_	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \mu Adc, I_E = 0$)	V _(BR) CBO	30	_	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	5.0	_	Vdc
Collector Cutoff Current $(V_{CB} = 20 \text{ Vdc}, I_E = 0)$	Ісво	_	50	nAdc
Emitter Cutoff Current $(V_{EB} = 3.0 \text{ Vdc}, I_C = 0)$	I _{EBO}	-	50	nAdc
ON CHARACTERISTICS	<u> </u>		•	
DC Current Gain (Note 3) $ (I_C = 2.0 \text{ mAdc, } V_{CE} = 1.0 \text{ Vdc)} $ $ (I_C = 50 \text{ mAdc, } V_{CE} = 1.0 \text{ Vdc)} $	h _{FE}	120 60	360 -	-
Collector – Emitter Saturation Voltage (Note 3) (I _C = 50 mAdc, I _B = 5.0 mAdc)	V _{CE(sat)}	_	0.3	Vdc
Base – Emitter Saturation Voltage (Note 3) (I _C = 50 mAdc, I _B = 5.0 mAdc)	V _{BE(sat)}	_	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS	<u>.</u>			
Current – Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	300	_	MHz
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	_	8.0	pF
Collector-Base Capacitance (I _E = 0, V _{CB} = 5.0 V, f = 1.0 MHz)	C _{cb}	_	4.0	pF
Small–Signal Current Gain (I_C = 2.0 mAdc, V_{CE} = 10 Vdc, R_S = 10 k Ω , f = 1.0 kHz)	h _{fe}	120	480	-
Current Gain – High Frequency (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz) (I_C = 2.0 mAdc, V_{CE} = 10 V, f = 1.0 kHz)	h _{fe}	3.0 120	_ 480	-
Noise Figure (I _C = 100 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz)	NF	-	5.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 µs, Duty Cycle = 2.0%.

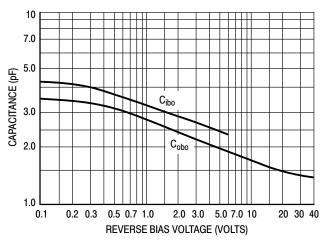


Figure 1. Capacitance

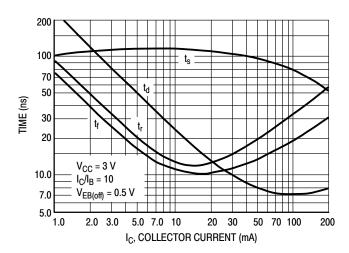


Figure 2. Switching Times

AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

 $(V_{CE} = 5 \text{ Vdc}, T_A = 25^{\circ}\text{C})$ Bandwidth = 1.0 Hz

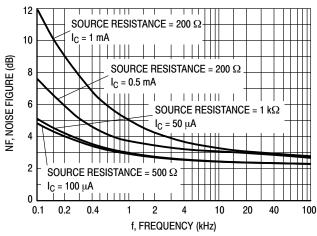


Figure 3. Frequency Variations

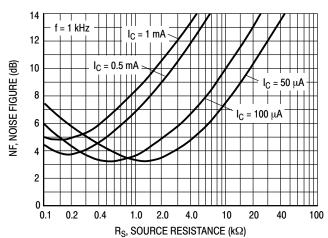
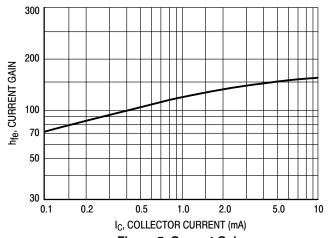


Figure 4. Source Resistance

h PARAMETERS

(V_{CE} = 10 V, f = 1 kHz, T_A = 25°C)



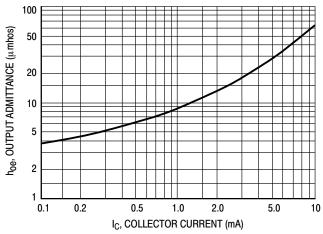


Figure 5. Current Gain

Figure 6. Output Admittance

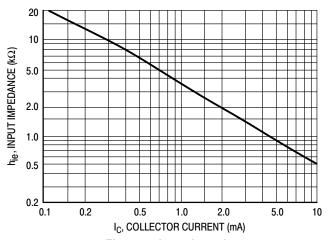


Figure 7. Input Impedance

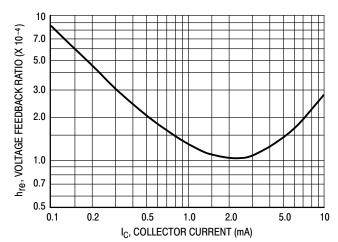


Figure 8. Voltage Feedback Ratio

STATIC CHARACTERISTICS

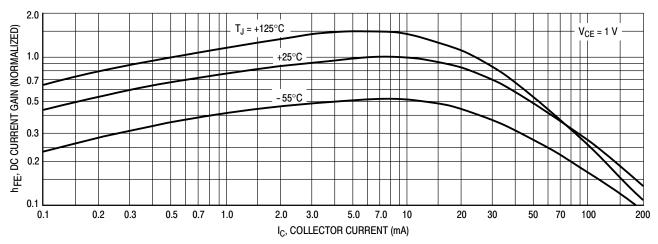


Figure 9. DC Current Gain

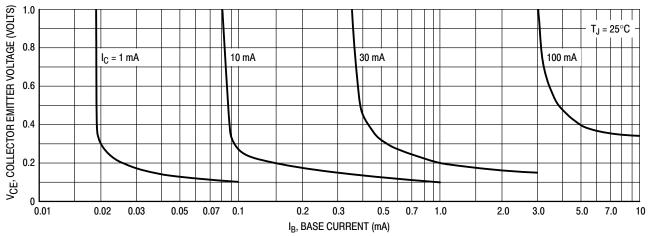


Figure 10. Collector Saturation Region

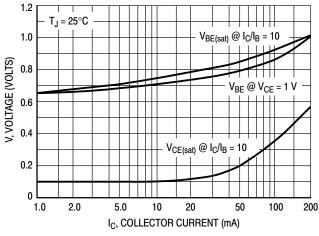


Figure 11. "On" Voltages

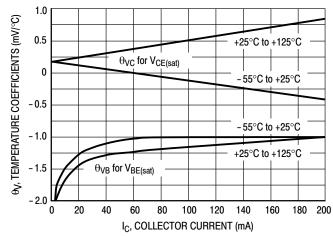


Figure 12. Temperature Coefficients

MILLIMETERS

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40





SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

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MAX

1.11

0.10

0.50

0.20

3.04

1.40

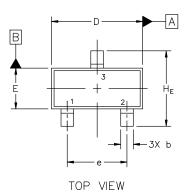
2.04

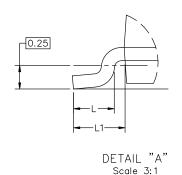
0.55

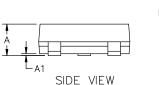
0.69

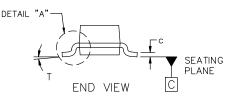
2.64

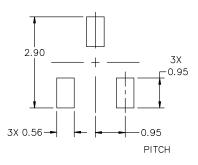
10°











NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package



* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODI	
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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